

Quench-switching of antiferromagnetic CuMnAs using ultrashort pulses

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HITACHI



Outline

Quench switching of magnetic state in CuMnAs

- Epitaxial CuMnAs – tetragonal, collinear AFM
- From spin-orbit based reorientation switching to quench switching of AFM
- Quench switching - strong GMR like signals (20% at RT, 100% at low T)
- Electrical Quench switching with pulses down to ns range
- Optical switching with 120fs laser pulses

Atomically sharp domain walls in CuMnAs

- Invisible domain walls in PEEM images
- Observation of atomically sharp domain walls by DPC-STEM

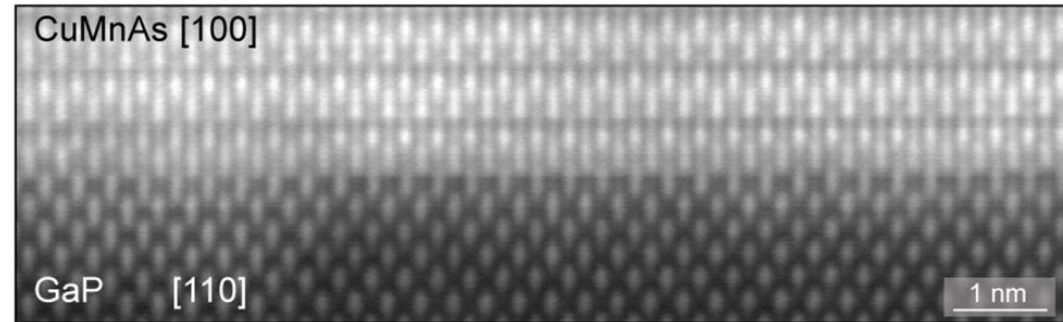
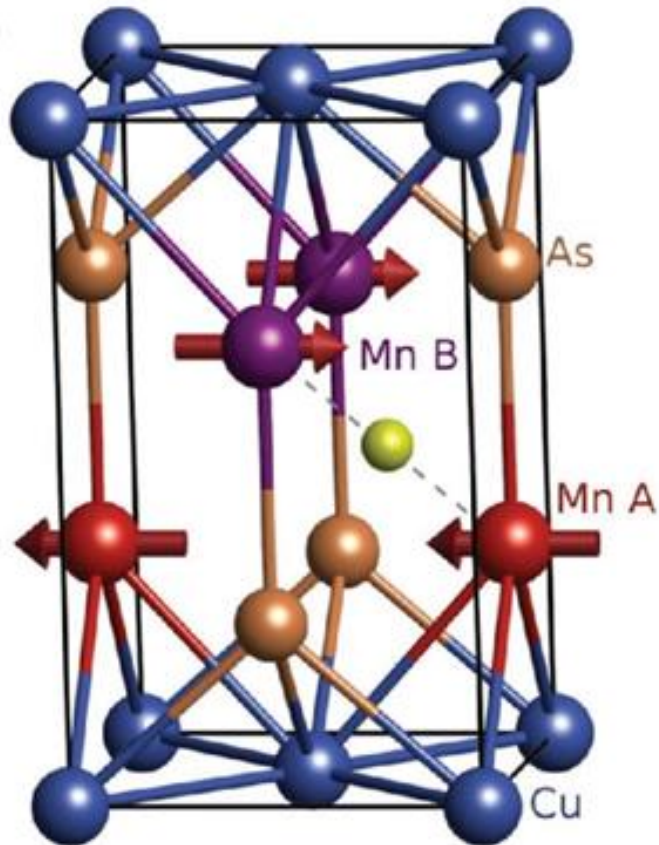
Temperature dependent relaxation

- Deterministic temperature dependent relaxation described by stretched exponentials

Functionality

- Write, read, erase functionality in a simple bar device
- Complex multilevel behaviour e.g. for Neuromorphic applications

Tetragonal antiferromagnetic CuMnAs

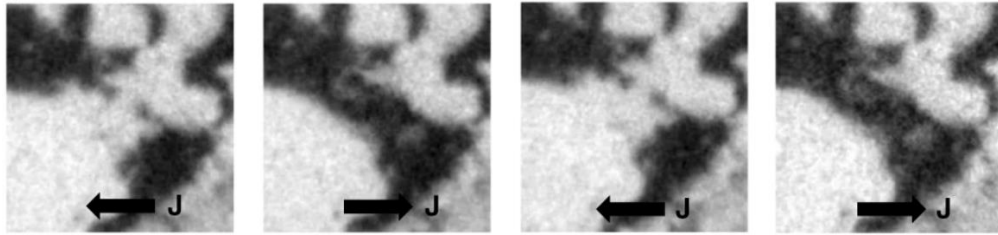


MBE growth on GaP (or GaAs, Si) substrates
Typical thickness 50nm

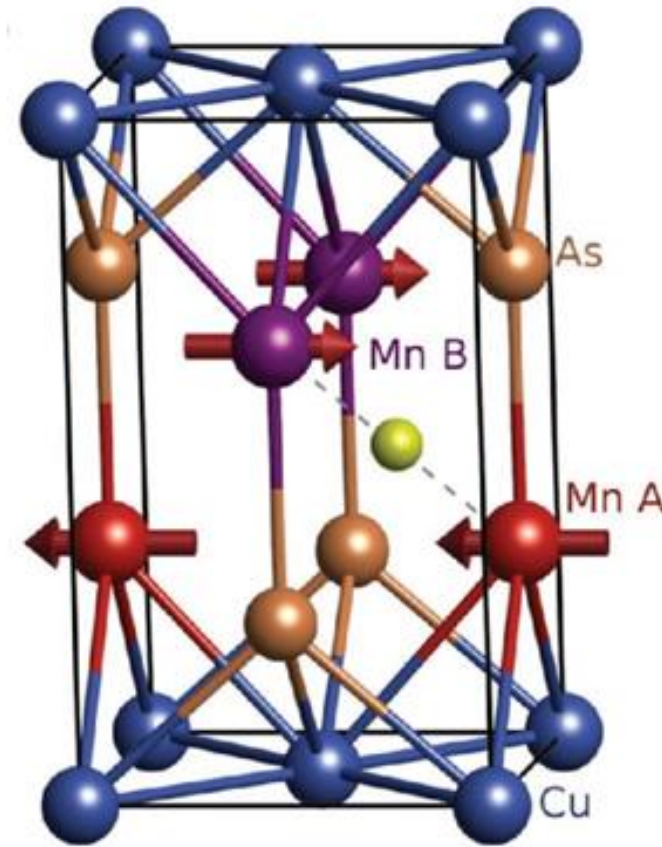
Collinear antiferromagnet with in-plane easy direction
 $T_N = 480\text{K}$

From reorientation to quench switching

Reorientation of L vector using staggered SO fields
Present in CuMnAs due to special symmetry
(inversion symmetry broken by magnetic order)



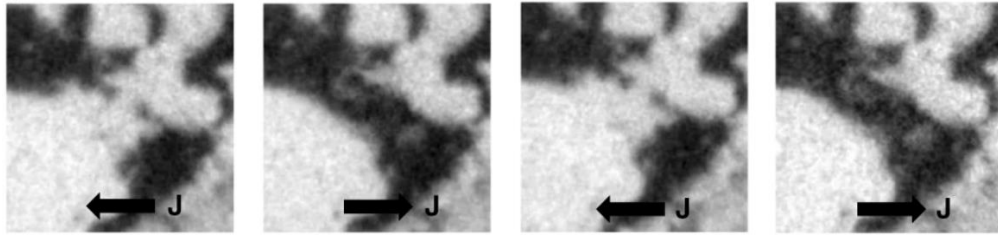
Reorientation observed by XMLD-PEEM
AMR electrical readout, signal amplitude $\sim 0.1\%$



Zelezny et al., PRL 2014
Wadley et al., Science 2016
Wadley et al., Nature Nanotech. 2018

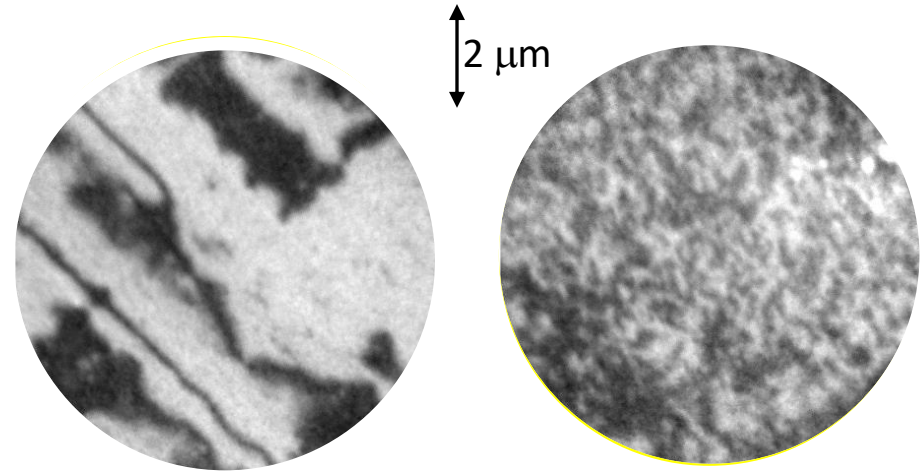
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Strong pulses – large resistivity changes

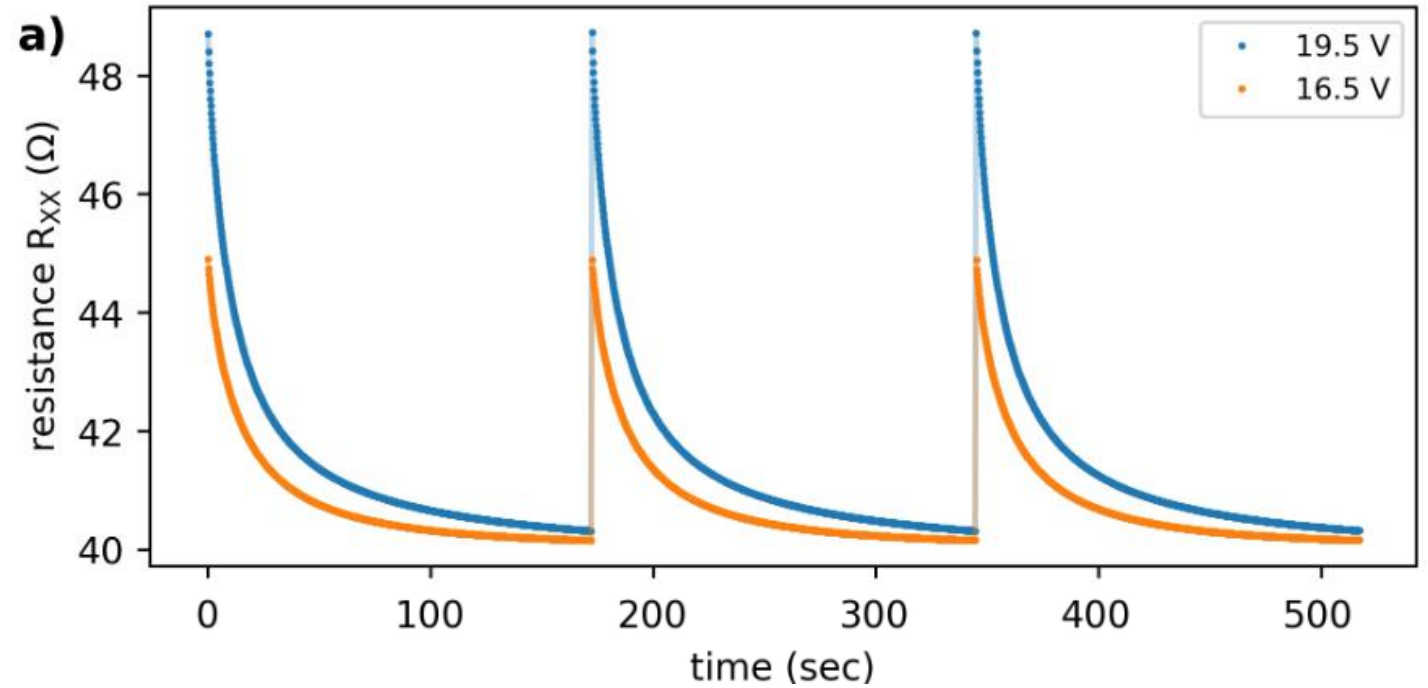
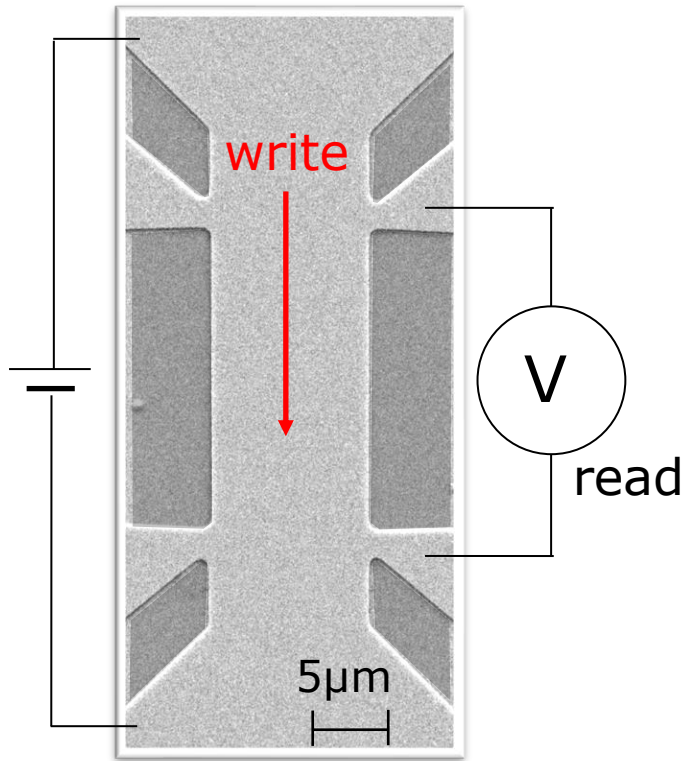


Quench-switching to metastable nano-textured magnetic state

Zelezny et al., PRL 2014
Wadley et al., Science 2016
Wadley et al., Nature Nanotech. 2018

Kaspar et al., Nature Electron (2020)

Quench switching of resistivity

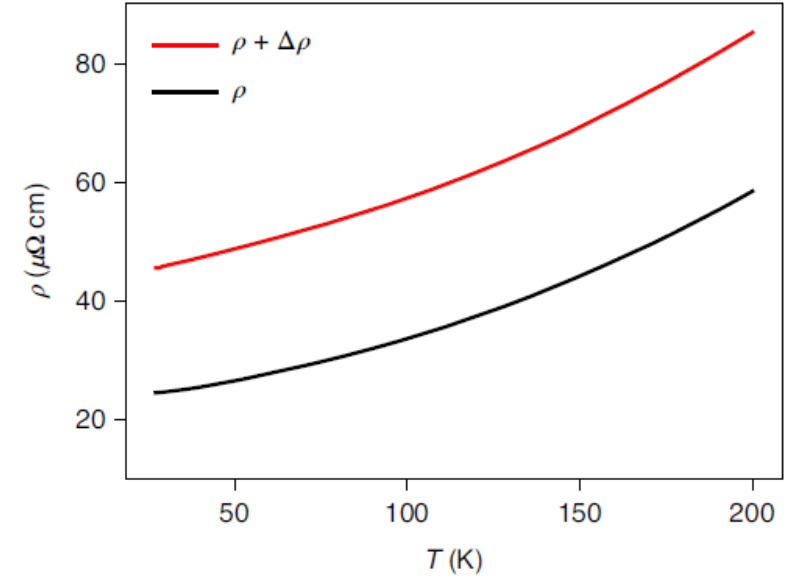
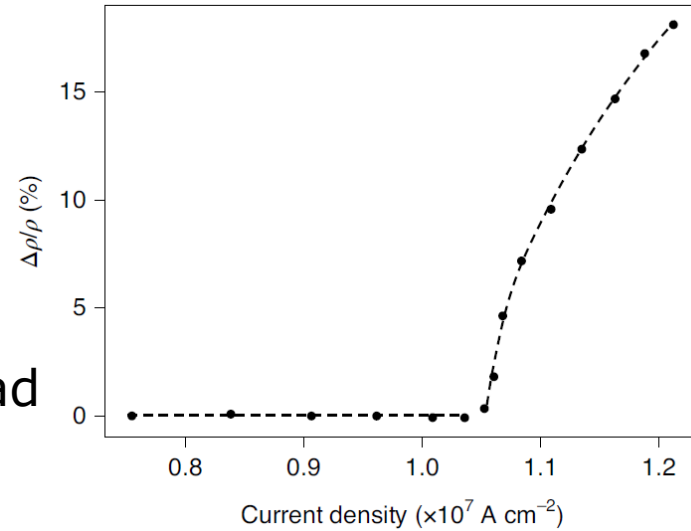
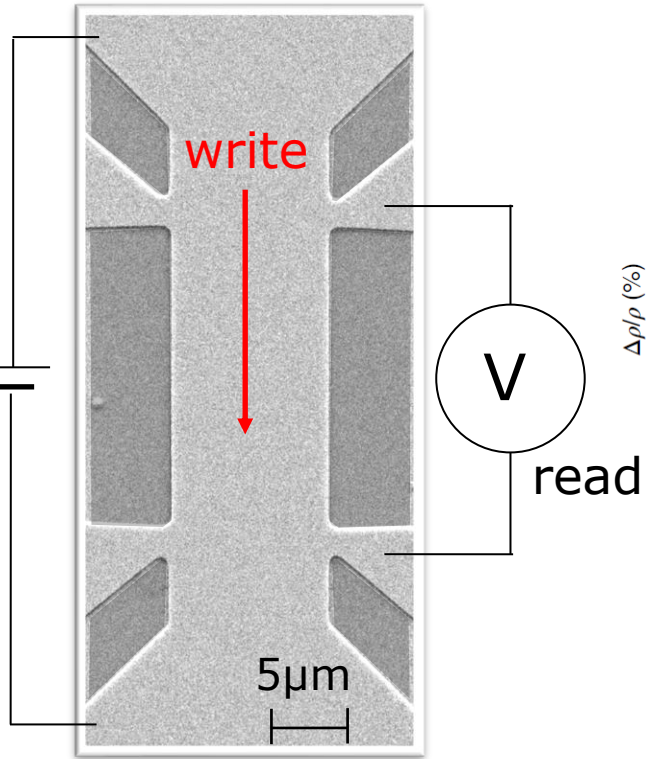


Maximum resistance change 20% at RT

Amplitude of quench switching signal

Write pulse amplitude

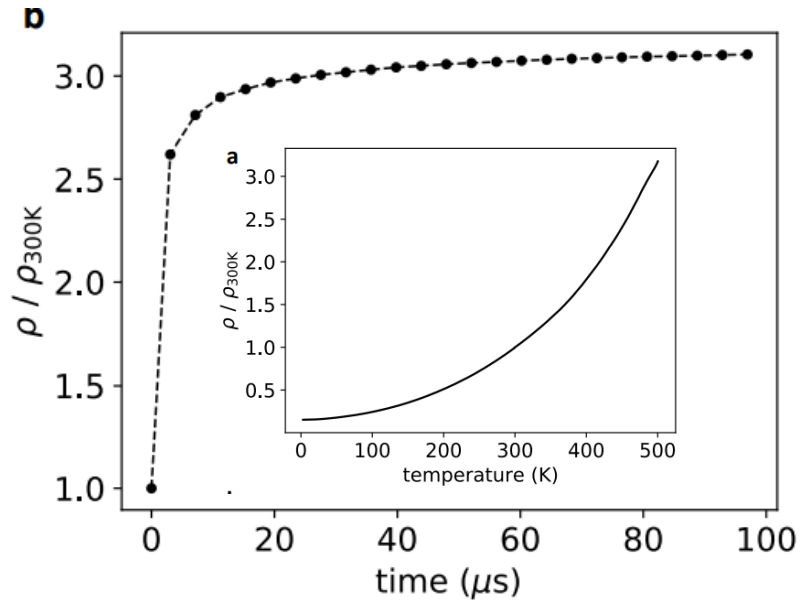
100% at low temperatures



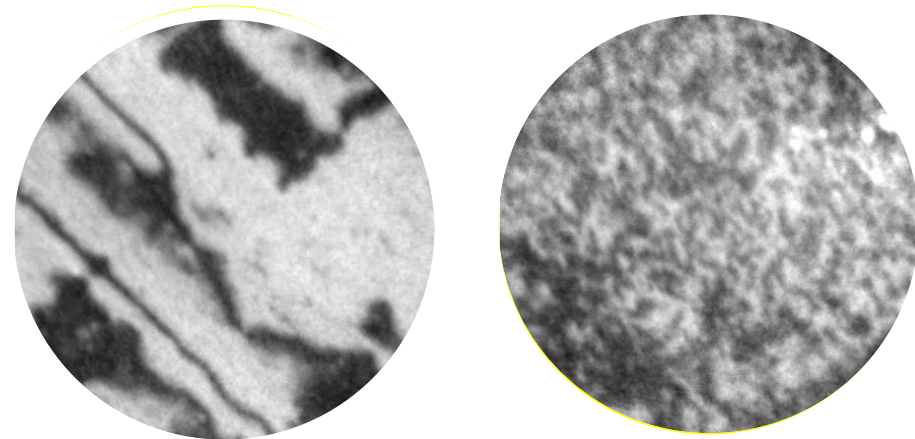
resistivity increase at low T corresponds to ab initio calculations of frozen random paramagnetic state - *Máca, et al., PRB 96, 094406 (2017)*

Mechanism of quench switching

Resistivity during 100 μs writing electrical pulse

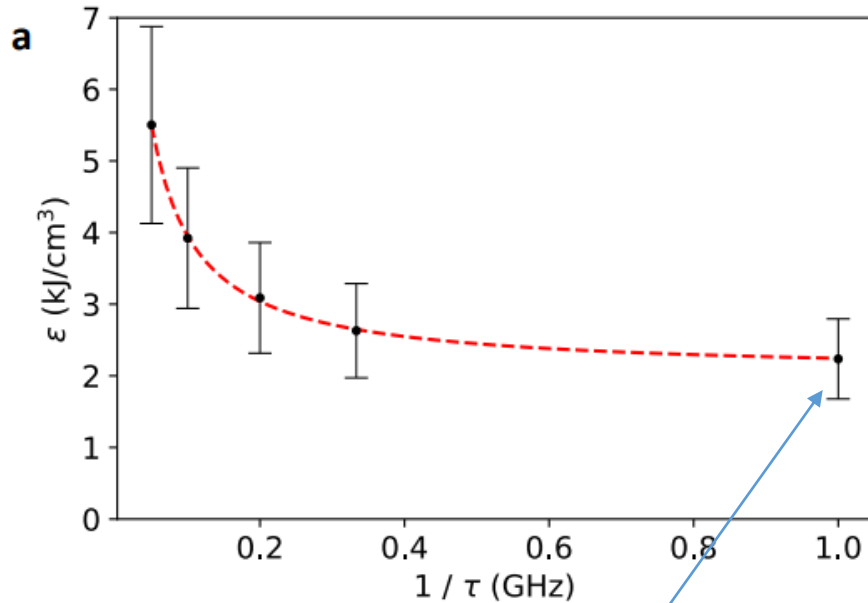


Temperature reaches during pulse T_N
Follows fast cooling – quench of disordered state



Short electrical and laser pulses

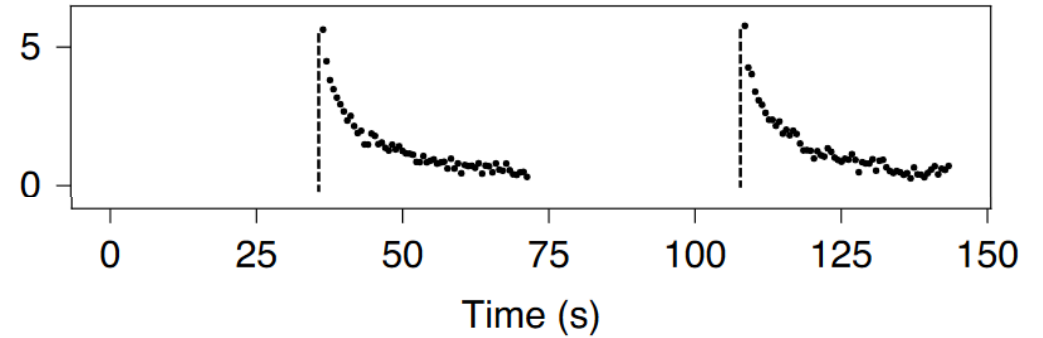
ns electrical pulses



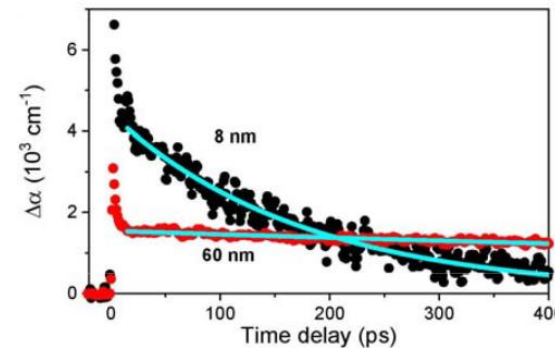
Energy needed to reach TN
(no time for heat dissipation)

100fs laser pulses

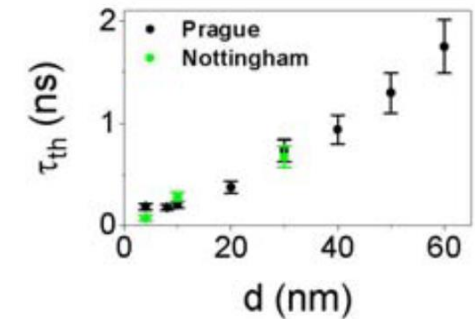
Absorbed energy density 2.6 kJ/cm³



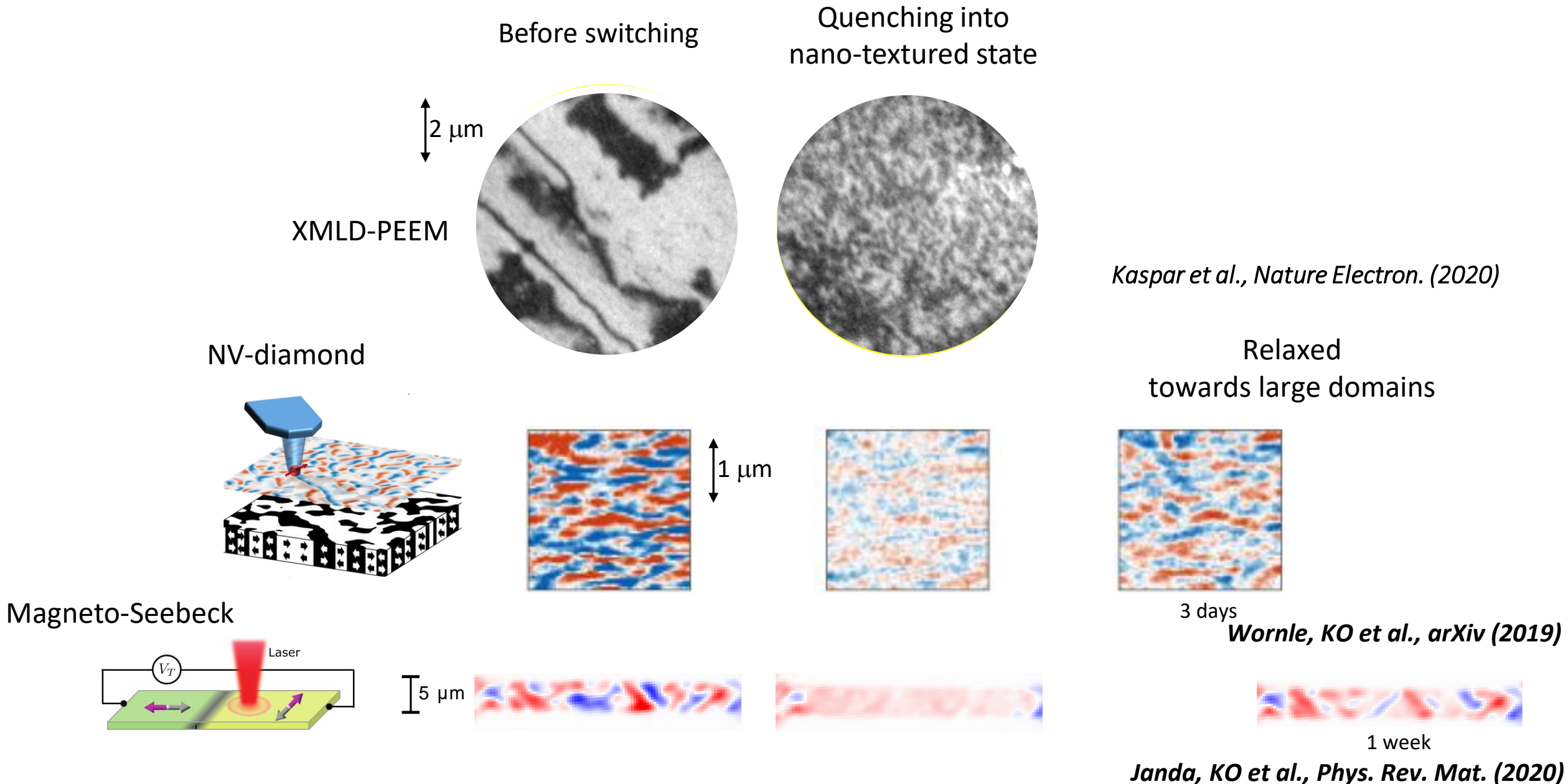
Optical detection of quench switching also possible



Cooling after pulse
(P&P experiment)



Magnetic imaging of nano-fragmentation in CuMnAs



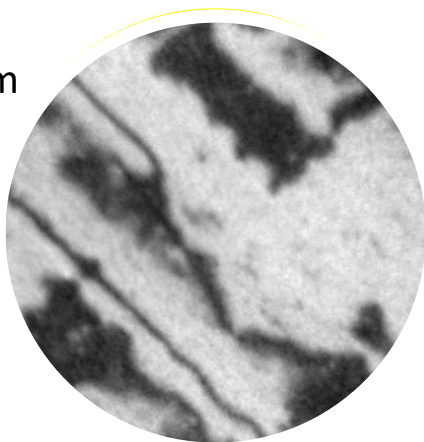
Magnetic imaging of nano-fragmentation in CuMnAs

**Micromagnetic DW
width 100nm**

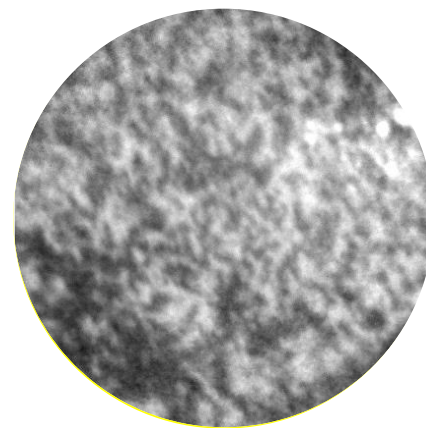
XMLD-PEEM

2 μm

Before switching



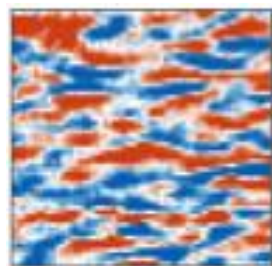
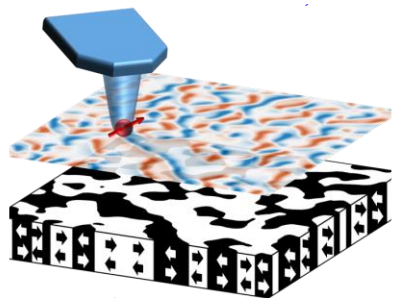
Quenching into
nano-textured state



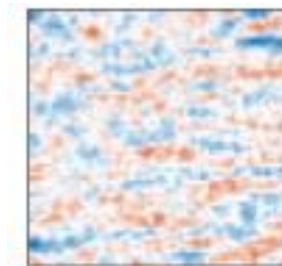
**Feature size below
~10nm resolution**

Kaspar et al., Nature Electron. (2020)

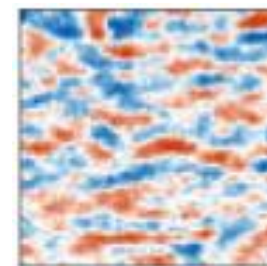
NV-diamond



1 μm



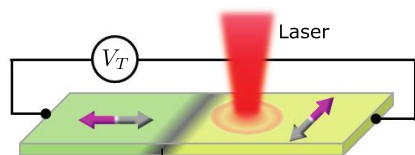
Relaxed
towards large domains



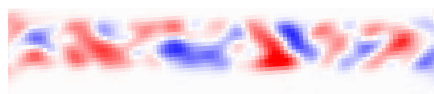
3 days

Wornle, KO et al., arXiv (2019)

Magneto-Seebeck



5 μm



1 week

Janda, KO et al., Phys. Rev. Mat. (2020)

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- **Invisible domain walls in PEEM images**
- **Observation of atomically sharp domain walls by DPC-STEM**

Temperature dependent relaxation

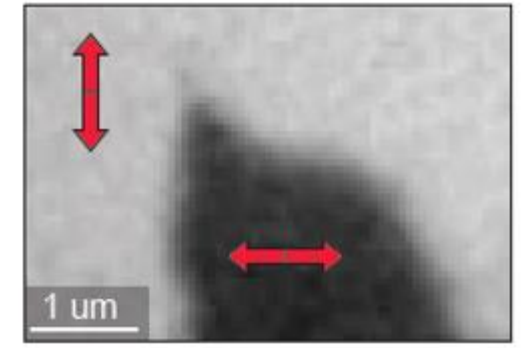
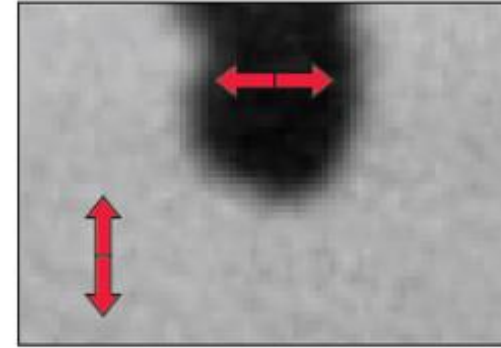
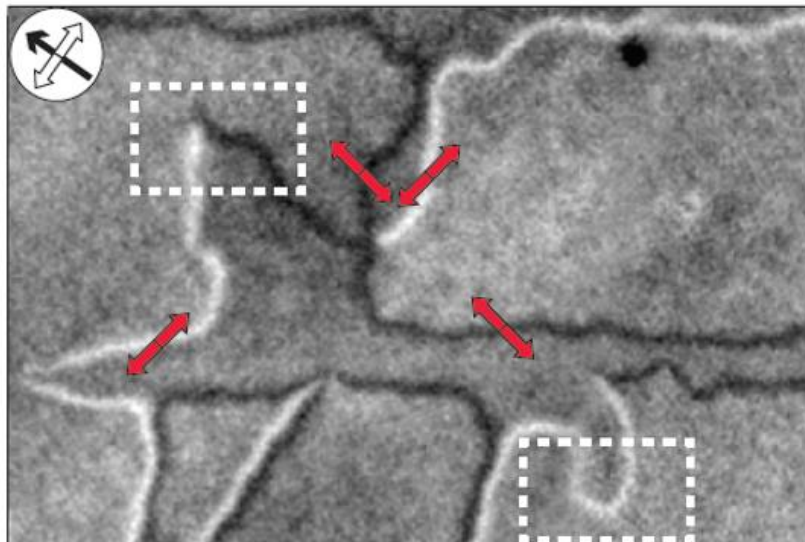
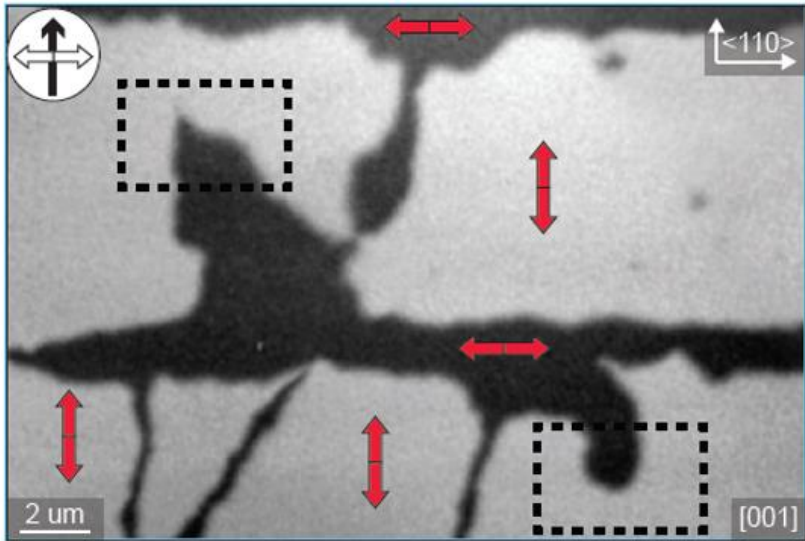
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Functionality

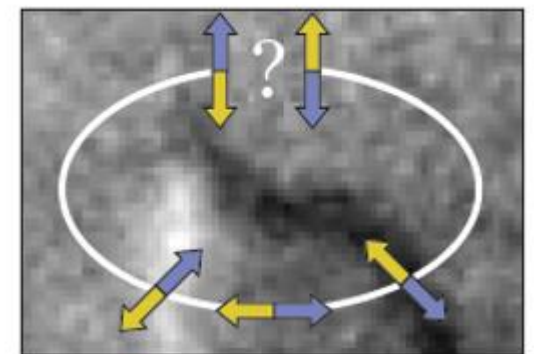
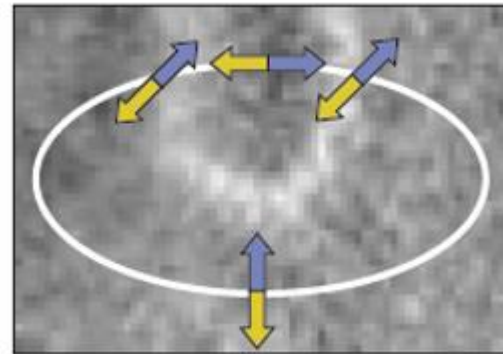
- Write, read, erase functionality in a simple bar device
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More PEEM imaging

↑ Beam direction \longleftrightarrow Beam polarization \longleftrightarrow Spin axis



Mn sublattice spin polarization



Micromagnetic 90° DWs

$$w_{\text{DW}} = 100\text{nm}$$

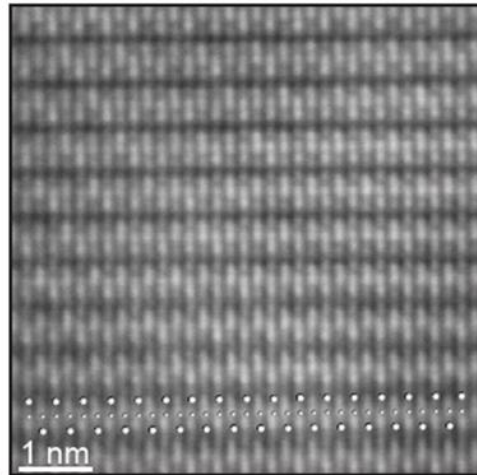
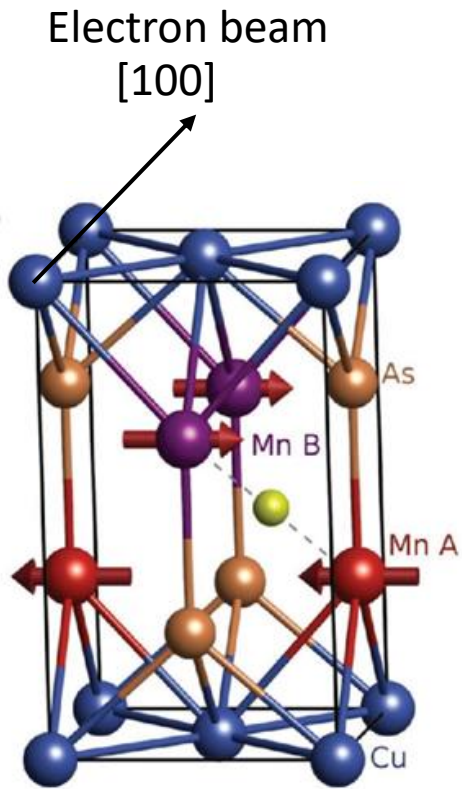
Invisible 180° DWs

$$w_{\text{DW}} \leq 10\text{nm}$$

Krizek, KO et al., arXiv (2020)

Atomically sharp DWs in DPC-STEM

Krizek et al., arXiv (2020)

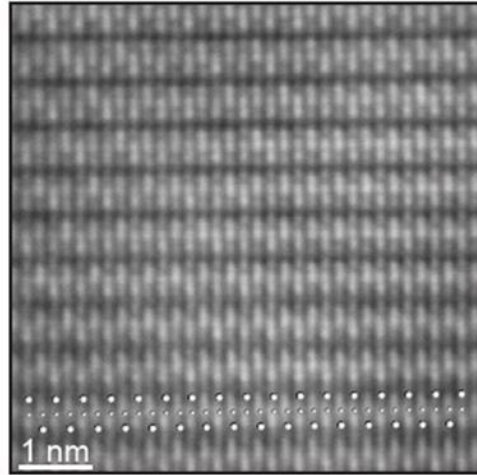
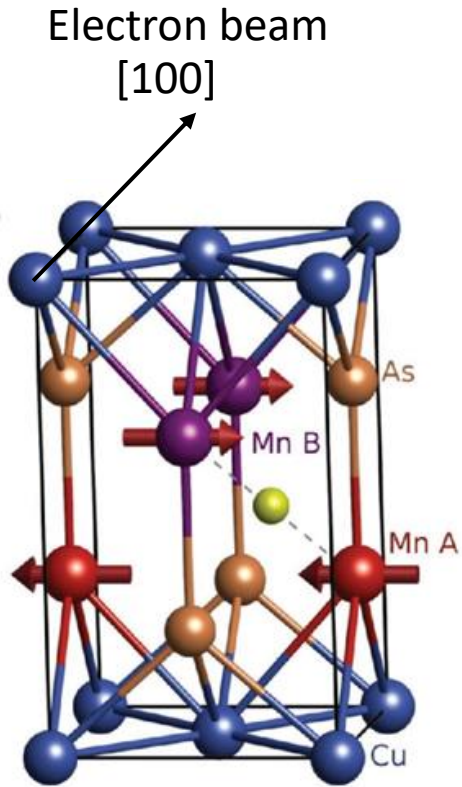


50-100nm lamella
Column of ~100 atoms

HAADF Detector ... electrons scattered by the column of atoms
(High Angle Annular Dark Field)

Atomically sharp DWs in DPC-STEM

Krizek et al., arXiv (2020)



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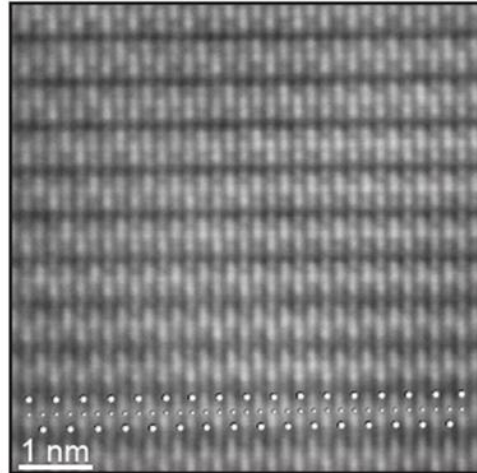
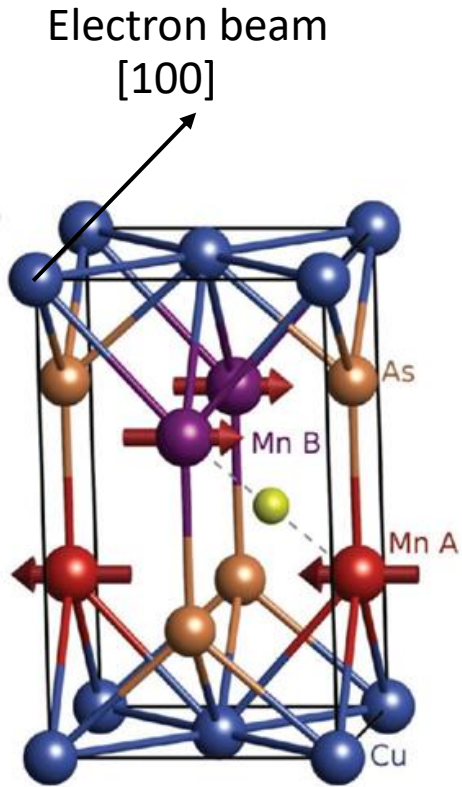
HAADF Detector ... electrons scattered by the column of atoms
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DPC Detector ... angular deviation of passing electrons
(Differential Phase Contrast) -> magnetic contrast on FM domains

All atoms in the column/plane has the same polarization

Atomically sharp DWs in DPC-STEM

Krizek et al., Sci. Adv. (2022)



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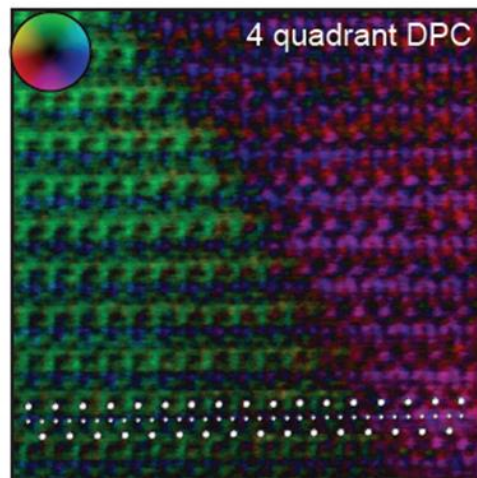
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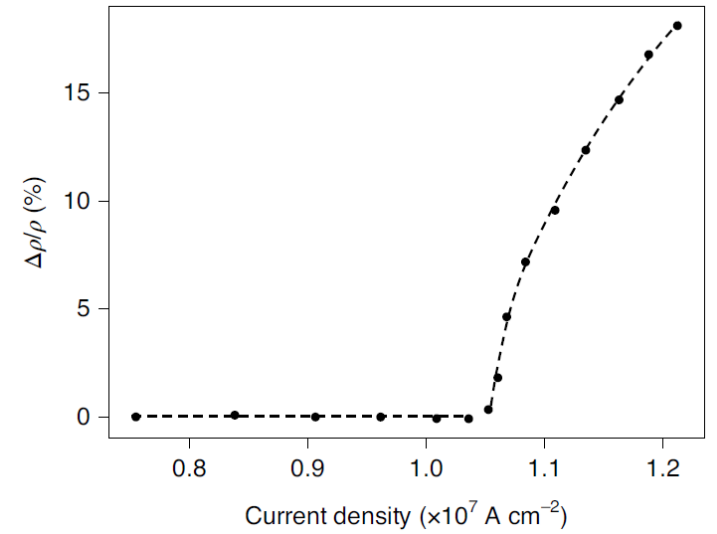
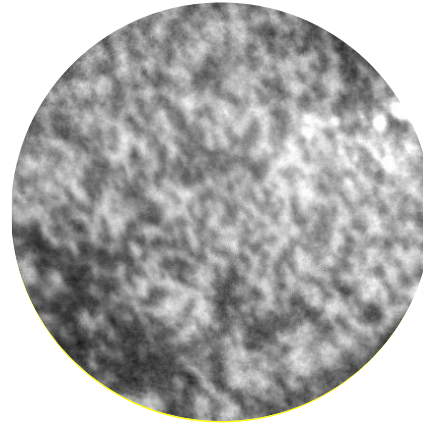
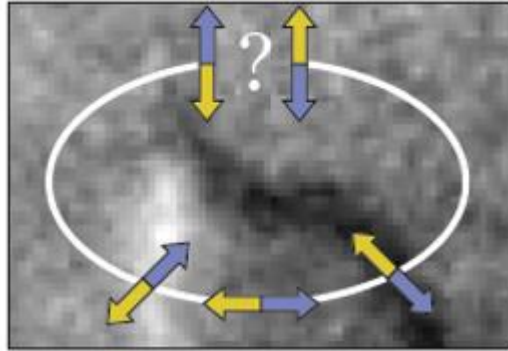
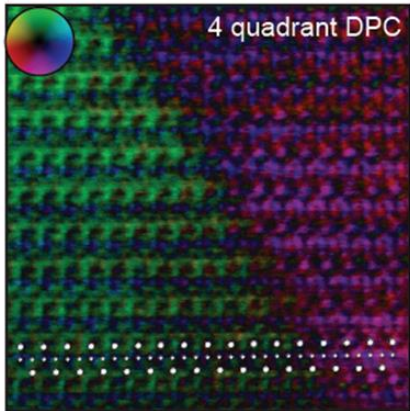
All atoms in the column/plane has the same polarization

Carefully excluded origin due to possible artefacts (abruptly varying strain, chemical composition, lamella thickness, crystal rotation, and formation of crystal grain overlaps)

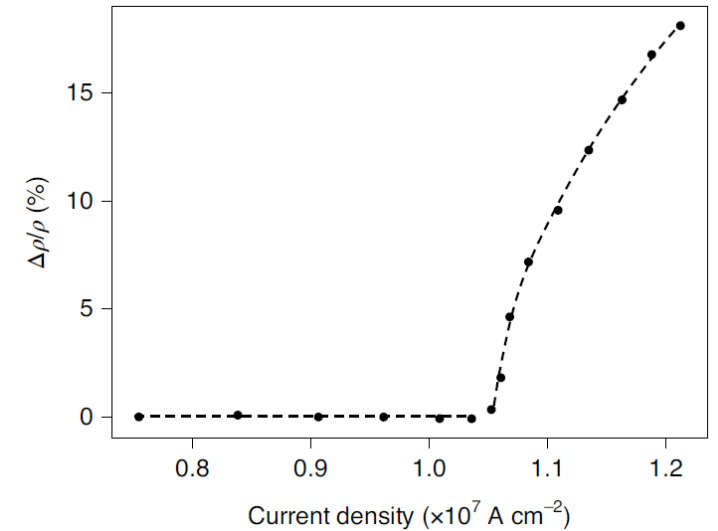
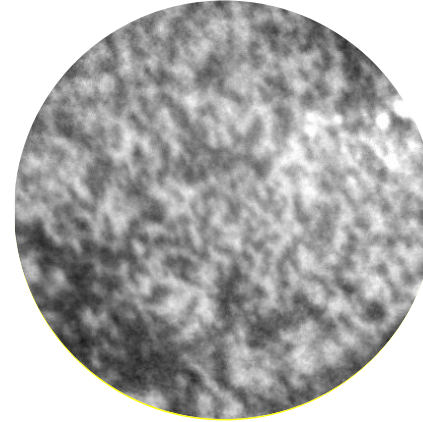
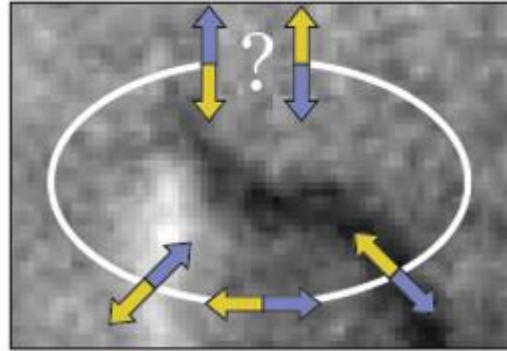
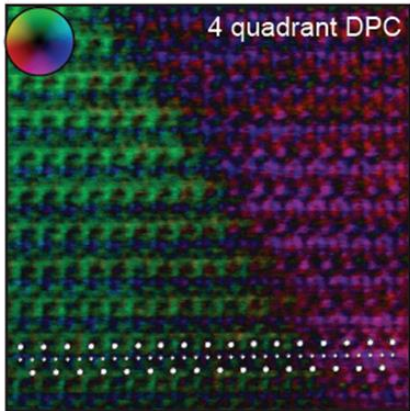
Dynamic diffraction calculations consistent with the observed contrast



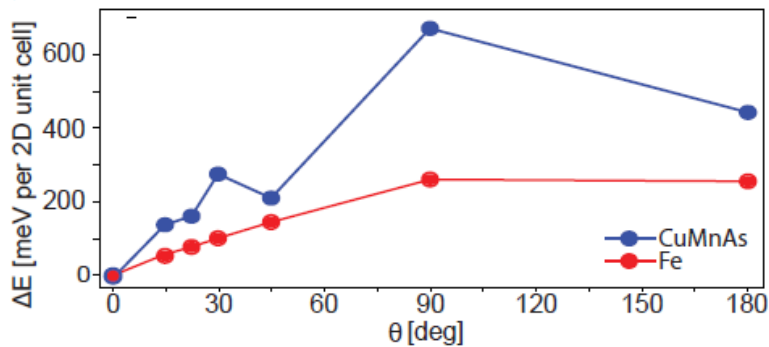
Atomically sharp domain walls



Atomically sharp domain walls



Ab-initio calculations of sharp domain walls



- Deviation from micromagnetic semiclassical exchange constant model
- Metastable magnetic configurations – enough to stabilise metastable quenched state
- In FMs obscured by long range dipolar interaction – quenching ineffective

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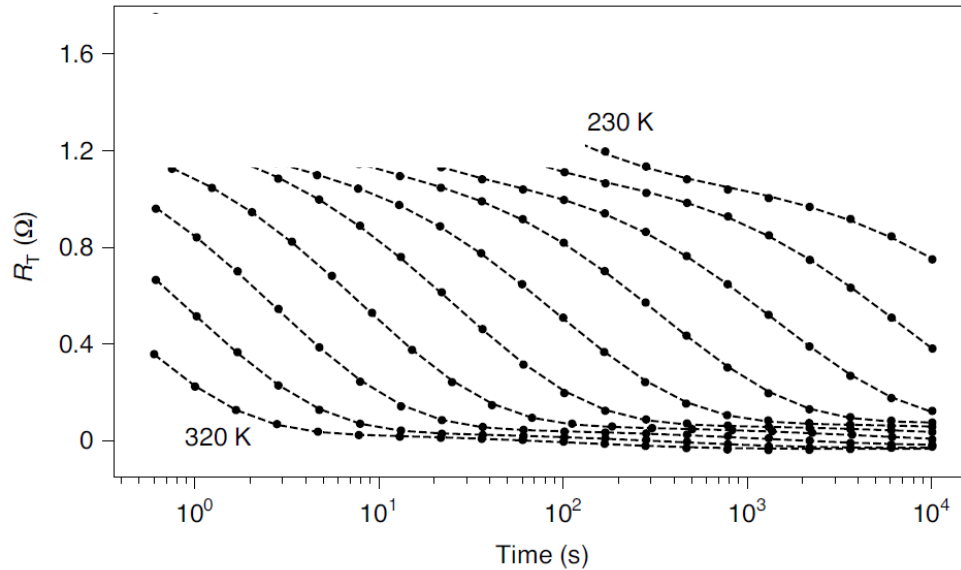
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Thermally activated relaxation – two main components



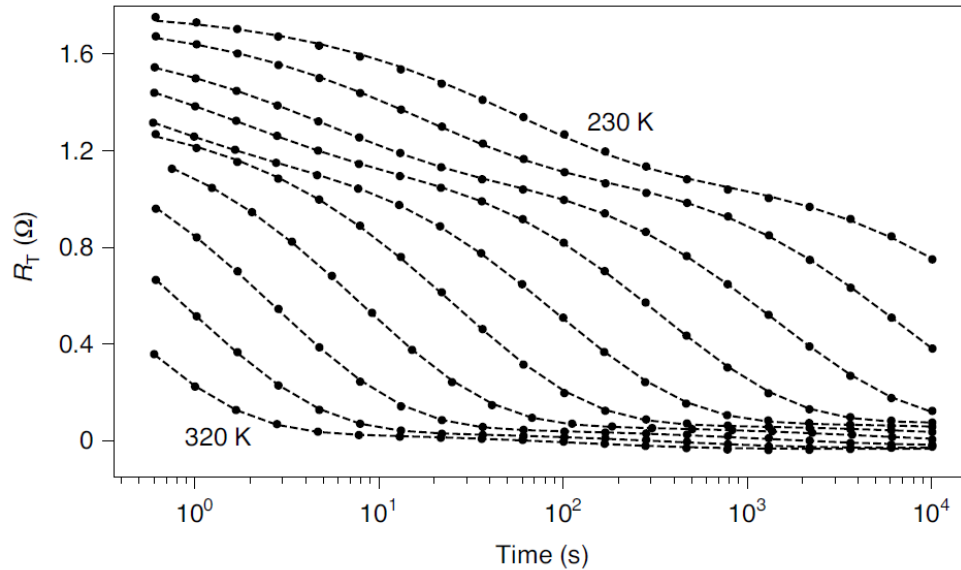
Relaxation well characterised by stretched exponential function :

$$R(t) = R_0 + \Delta R \cdot e^{-\left(\frac{t}{\tau}\right)^{3/5}}$$

Exponent 3 / 5 -> in complex interacting 3D system

Phillips J. Non-cryst. Sol. ,2006

Thermally activated relaxation – two main components



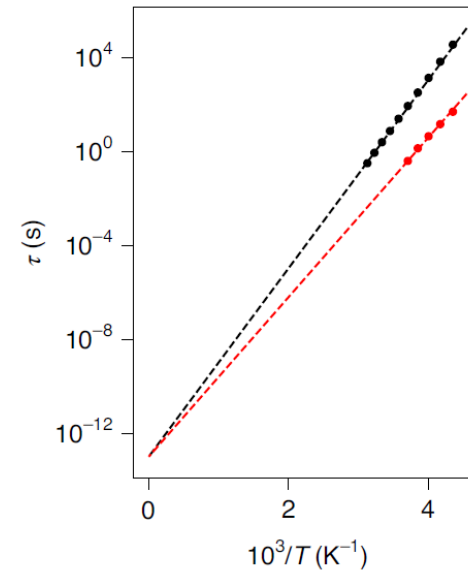
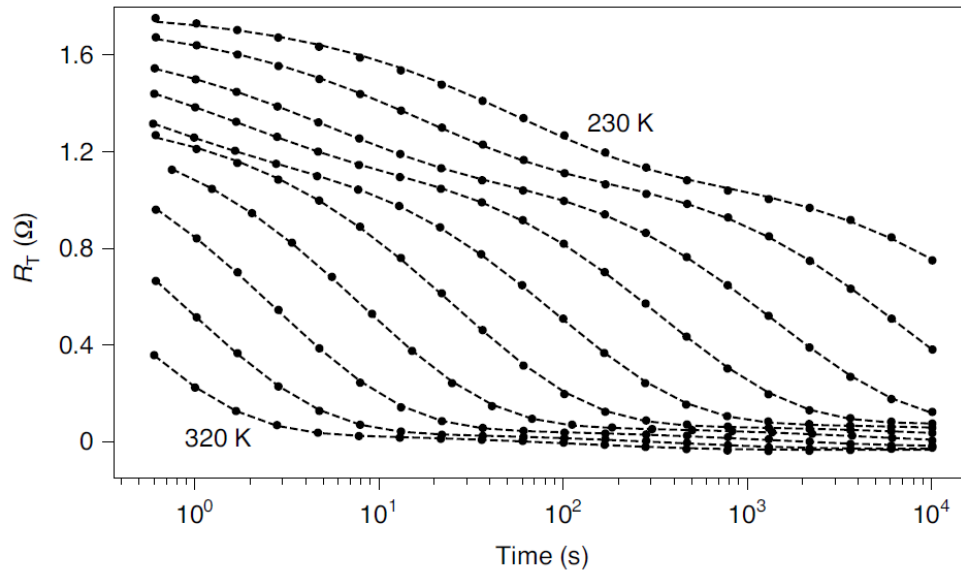
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Thermally activated relaxation – two main components



$$\tau = \tau_0 \cdot e^{\frac{E_A}{k_B T}}$$

Two main components:
10s and 10ms at RT

Activation energy

$$E_{A1}/k_B = 30.8 \times 300 \text{ K}$$

$$E_{A2}/k_B = 26.1 \times 300 \text{ K}$$

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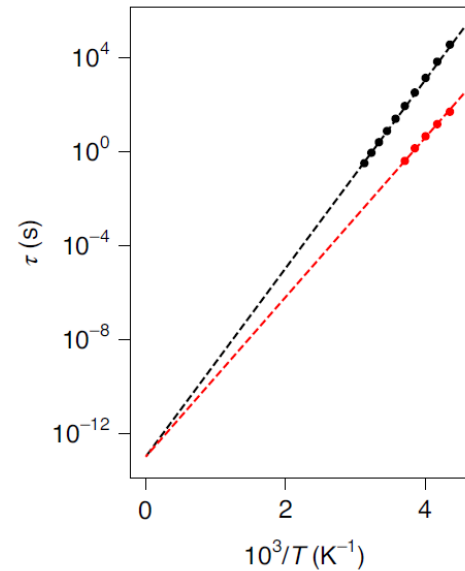
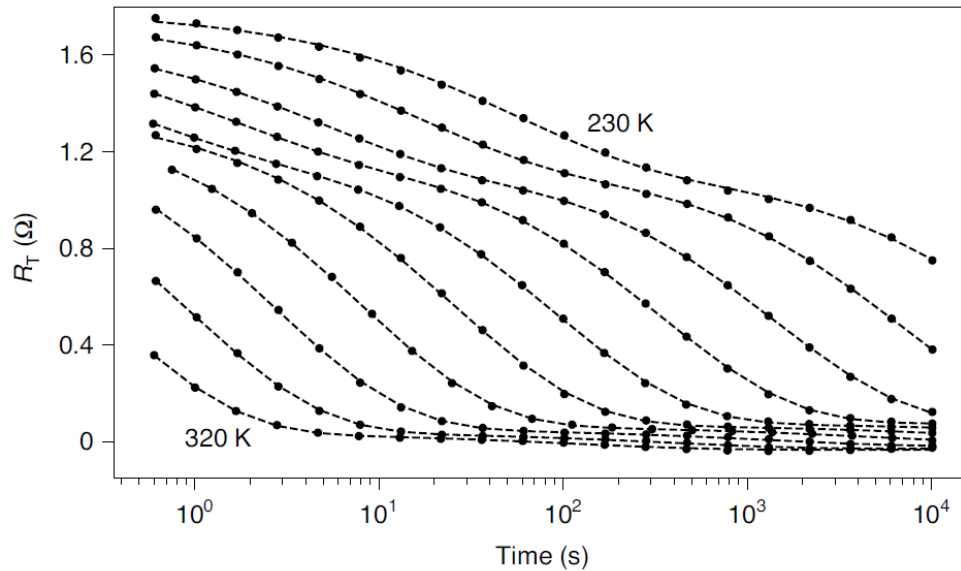
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1 / τ₀ in THz range -> antiferromagnetic dynamics

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ULTRAFAST relaxation

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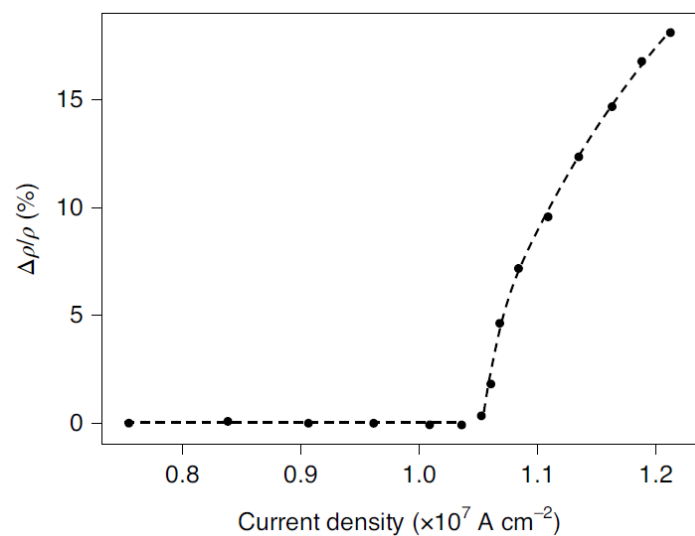
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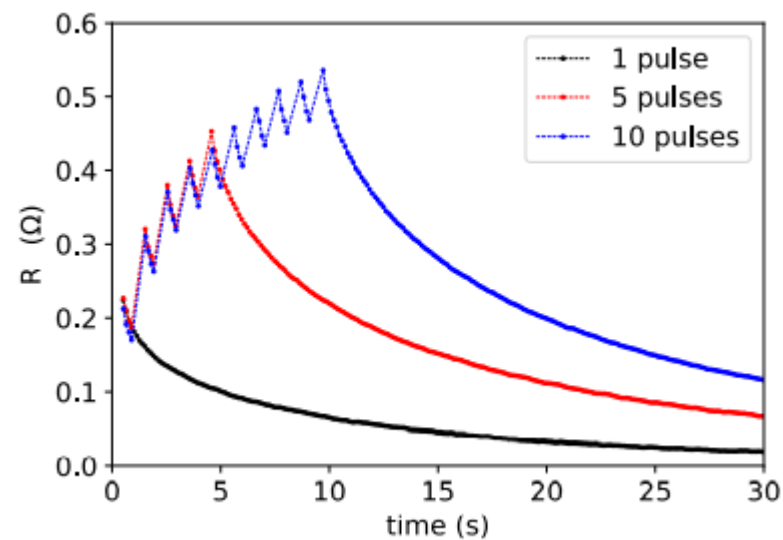
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Multilevel character of quench switching

Strength of writing pulse

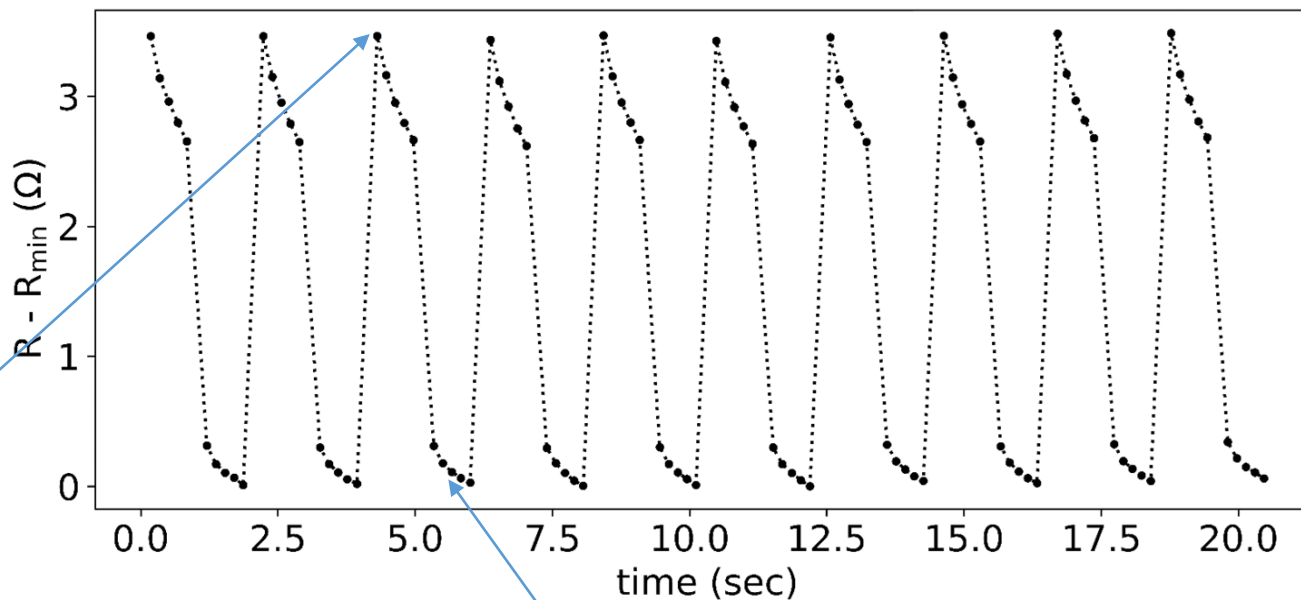
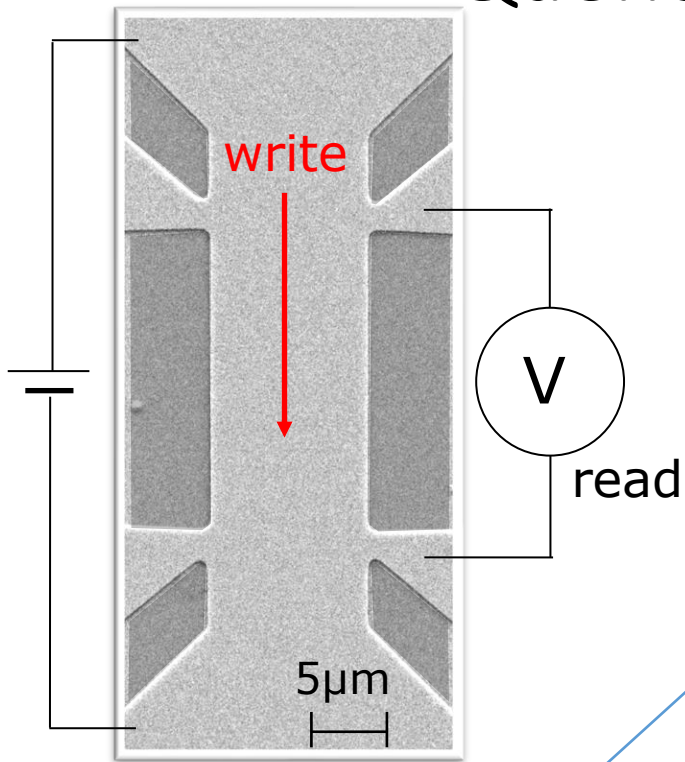


Pulse counter functionality



1ns pulses

Quench-switching / erasing experiment



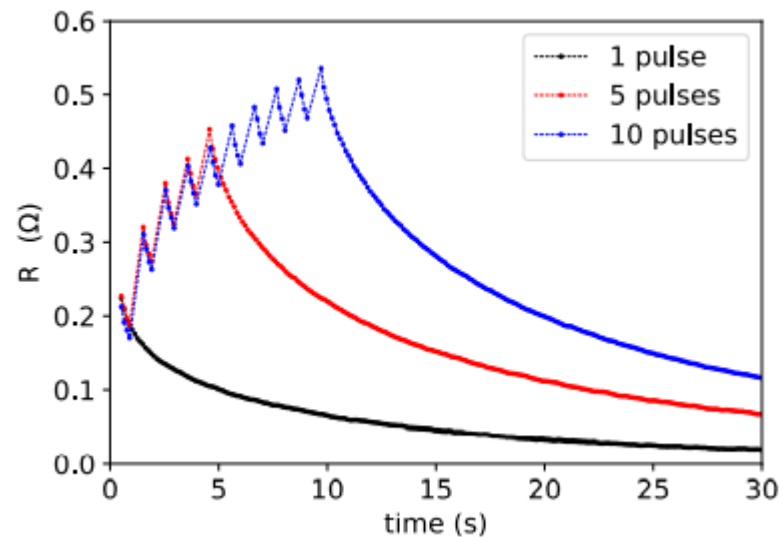
High current density

- high peak temperature
- quenching of strongly fragmented state

Lower current density

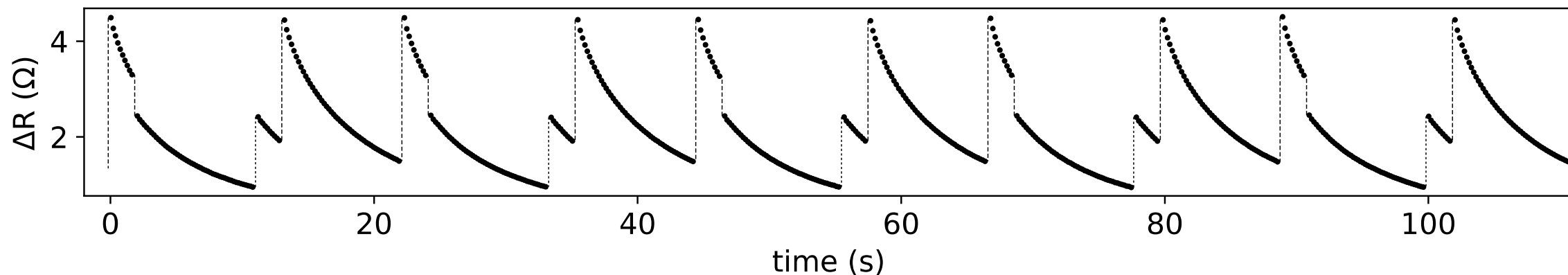
- lower peak temperature
- acceleration of thermally activated relaxation

Potential for neuromorphic computation



Multilevel - analogue memory (synapses)

Response depend on number, delay, order of pulses (neuron)



List of co-authors:

Kaspar, KO et al., Nature Electron (2020)

Quenching of an antiferromagnet into high resistivity states using electrical or ultrashort optical pulses

Z. Kašpar^{1,2}, M. Surýnek², J. Zubáč^{1,2}, F. Krizek¹, V. Novák¹, R. P. Champion³, M. S. Wörnle^{4,5}, P. Gambardella⁴, X. Marti¹, P. Němec², K. W. Edmonds³, S. Reimers^{3,6}, O. J. Amin³, F. Maccherozzi⁶, S. S. Dhesi⁶, P. Wadley³, J. Wunderlich^{1,7}, K. Olejník¹ and T. Jungwirth^{1,3}✉

Křížek et al, Sci. Adv. (2022)

Atomically sharp domain walls in an antiferromagnet

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Thank you for your attention